

TRANSISTOR (NPN)

FEATURES

- For AF driver and output stages
- High collector current
- Low collector-emitter saturation voltage
- Complementary types: BCP51 ... BCP53 (PNP)

SOT-223



- 1. BASE
- 2. COLLECTOR
- 3. EMITTER

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	BCP54	BCP55	BCP56	Units
V _{CBO}	Collector-Base Voltage	45	60	100	V
V _{CEO}	Collector-Emitter Voltage	45	60	80	V
V _{EBO}	Emitter-Base Voltage	5		V	
Ic	Collector Current -Continuous	1			Α
Pc	Collector Power Dissipation	1.5		W	
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	94		°C/W	
T _{stg}	Storage Temperature Range	-65to+150		$^{\circ}$	

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter		Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	BCP54			45		
	BCP55	$V_{(BR)CBO}$	I _C = 0.1mA,I _E =0	60		V
	BCP56			100		
Collector-emitter breakdown voltage	BCP54			45		
	BCP55	$V_{(BR)CEO}$	I _C = 10mA,I _B =0	60		V
	BCP56			80		
Base-emitter breakdown voltage		$V_{(BR)EBO}$	I _C = 10μΑ,I _E =0	5		V
Collector cut-off current		I _{CBO}	V _{CB} = 30 V, I _E =0		100	nA
		h _{FE(1)}	V _{CE} = 2V, I _C =5mA	25		
DC current gain		h _{FE(2)}	V _{CE} = 2V, I _C =150m A	63	250	
		h _{FE(3)}	V _{CE} = 2V, I _C =500m A	25		
Collector-emitter saturation voltage		V _{CE(sat)}	I _C =500mA,I _B =50mA		0.5	V
Base-emitter voltage		V_{BE}	V _{CE} =2V, I _C =500m A		1	V
Transition frequency		f _T	V _{CE} =10V,I _C =50mA,f=100MHz	100		MHz

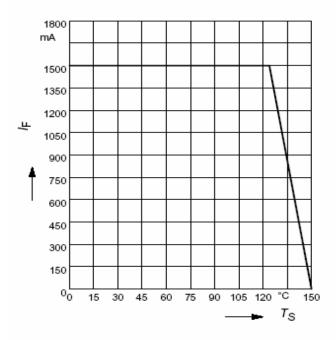
CLASSIFICATION OF hFE(2)

Rank	BCP54-10, BCP55-10, BCP56-10	BCP54-16, BCP55-16, BCP56-16		
Range 63-160		100-250		



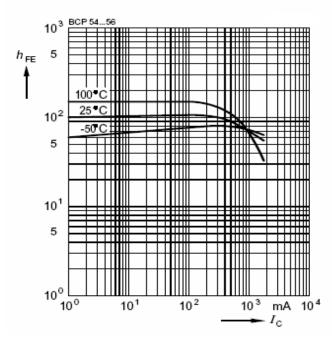
Typical Characteristics

Total power dissipation $P_{tot} = f(T_S)$



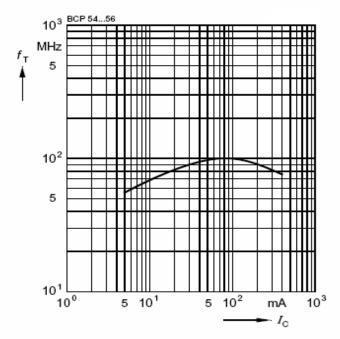
DC current gain $h_{FE} = f(I_C)$

$$V_{CE} = 2V$$



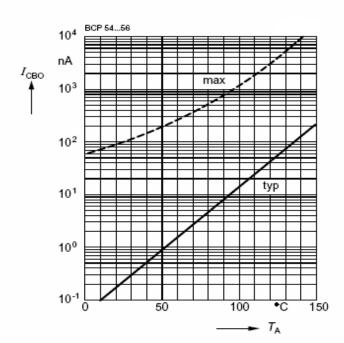
Transition frequency $f_T = f(I_C)$

$$V_{CE} = 10V$$



Collector cutoff current $I_{CBO} = f(T_A)$

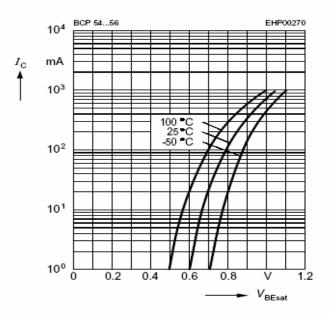
$$V_{CB} = 30V$$





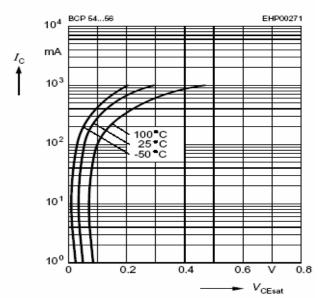
Base-emitter saturation voltage

$$I_{C} = f(V_{BEsat}), h_{FE} = 10$$



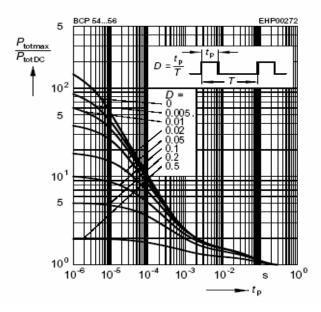
Collector-emitter saturation voltage

$$I_{\text{C}} = f(V_{\text{CEsat}}), h_{\text{FE}} = 10$$



Permissible pulse load

 $P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by SLKORMICRO manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B